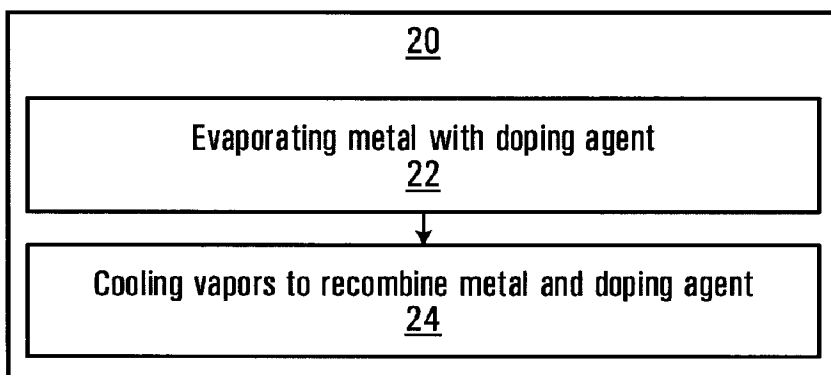




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(54) Titre : POUDRES METALLIQUES DESTINEES A UNE UTILISATION COMME MATERIAU D'ELECTRODE DANS LES CONDENSATEURS EN CERAMIQUE MULTICOUCHES ET METHODE DE FABRICATION ET UTILISATION ASSOCIEE
 (54) Title: METALLIC POWDERS FOR USE AS ELECTRODE MATERIAL IN MULTILAYER CERAMIC CAPACITORS AND METHOD OF MANUFACTURING AND OF USING SAME



(57) **Abrégé/Abstract:**

The present disclosure generally relates to metallic powders for use in multilayer ceramic capacitors, to multilayer ceramic capacitors containing same and to methods of manufacturing such powders and capacitors. The disclosure addresses the problem of having better controlled smaller particle size distribution, with minimal contaminant contents which can be implemented at an industrial scale.

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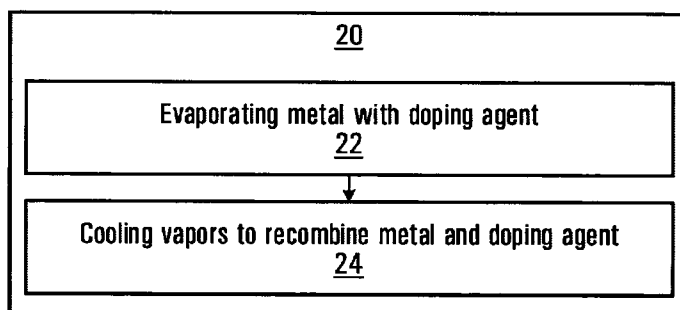


FIG. 1

(57) Abstract: The present disclosure generally relates to metallic powders for use in multilayer ceramic capacitors, to multilayer ceramic capacitors containing same and to methods of manufacturing such powders and capacitors. The disclosure addresses the problem of having better controlled smaller particle size distribution, with minimal contaminant contents which can be implemented at an industrial scale.

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5 **METALLIC POWDERS FOR USE AS ELECTRODE MATERIAL IN MULTILAYER
CERAMIC CAPACITORS AND METHOD OF MANUFACTURING AND OF USING
SAME**

CROSS-REFERENCE TO RELATED APPLICATION

[001] The present application claims the benefit of U.S. provisional patent application serial
10 number 62/623,708 filed on January 30, 2018.

FIELD OF TECHNOLOGY

[002] The present disclosure generally relates to metallic powders for use as electrode
material in multilayer ceramic capacitors, to multilayer ceramic capacitors containing same and to
methods of manufacturing such powders and capacitors.

15 **BACKGROUND INFORMATION**

[003] Recently, in mobile electronic equipment such as cellular phones and personal
computers, trends toward miniaturization, higher performance, and lower electric power
consumption have become increasingly prominent. Integration and miniaturization into chips of
passive components such as capacitors, inductors, and resistors used in these pieces of equipment
20 have also been accelerated. Conventionally, single-layer ceramic capacitors such as disk and
cylindrical-type capacitors have been primarily used. However, the use of multilayer ceramic
capacitors (MLCCs) prevails nowadays, because of their properties of high capacitance with small
size, high reliability, and excellent high-frequency characteristics. The quantity of shipment of
MLCCs has grown annually due to the rapid increase of the production of cellular phones and
25 computers, and the demand will further increase in the future.

[004] Traditional MLCCs use copper for their external electrodes, noble metals such as silver
or palladium for their inner electrodes and a ceramic acting as the dielectric. Over the past years,
nickel electrodes have been replacing palladium bearing electrodes. This limited the reliance on
palladium, which was relatively expensive, and enabled MLCC manufacturers to cost

5 effectively produce MLCC in much higher capacitance ranges and compete with manufacturers of tantalum capacitors and other electrolytic capacitors.

[005] Base metals used for manufacturing the electrodes are typically provided in paste or in powder. The base metals generally need to be sintered to form the internal electrodes of MLCCs. However, in order to produce relatively small MLCCs, to control the capacitance of the
10 MLCCs in a relatively precise manner, and to facilitate the manufacturing of the MLCCs, the base metal needs to be provided in particles of a relatively small size, with a relatively low concentration of contaminants, and the size of the base metal needs to be relatively tightly controlled.

[006] JP 2004-292950 has proposed a nickel-based fine powder in which the average
15 particle diameter is ranging from 0.05 μm to 0.3 μm . However, the manufacturing process described in JP 2004-292950 makes use of a vapor phase reduction of nickel chloride vapor which results in a metallic powder contaminated with chlorine. In order to remove the chlorine, it is necessary to rinse with water, which increases particle aggregation and results in a particle size distribution which is skewed towards larger particle media sizes. This is why the number of
20 particles obtained in JP 2004-292950 that have a particle diameter of 0.6 times or smaller than the average particle diameter is 10% or less and that particles having a size of 1 μm or more can be as high as 721 ppm.

[007] JP 2001-073007 has proposed a nickel-based fine powder having an average particle diameter ranging from of 0.1 μm to 1.0 μm and having a coarse particle having a particle
25 diameter of 2 μm or more of 700 ppm. Similarly to the situation in JP 2004-292950, this document makes use of a vapor phase reduction of nickel chloride vapor which results in a metallic powder contaminated with chlorine. In order to remove the chlorine, it is necessary to rinse with water, which increases particle aggregation and results in a particle size distribution which is also skewed towards larger particle media sizes.

30 [008] The metallic powders and process of manufacturing same proposed in these documents are, therefore, not satisfactory due to the presence of larger particle size which increases the probability of defective products occurrence at the time of manufacturing MLCCs.

5 [009] As such, there is still a need in the field for metallic powders for use in multilayer ceramic capacitors that have a better controlled smaller particle size distribution and that can be produced efficiently and cost effectively on an industrial scale.

SUMMARY OF DISCLOSURE

[010] This Summary is provided to introduce a selection of concepts in a simplified form that are further described below in the Detailed Description. This Summary is not intended to identify
10 key aspects or essential aspects of the claimed subject matter.

[011] As embodied and broadly described herein, the present disclosure relates to a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the composition comprising metal-based spherical particles doped with a doping agent
15 that operates to increase the sintering temperature of the composition, and comprising less than 1000 ppm of carbon content, wherein the particles have a median size (D50) of ≤ 120 nm.

[012] As embodied and broadly described herein, the present disclosure relates to a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the composition comprising metal-based spherical particles doped with a doping agent
20 that operates to increase the sintering temperature of the composition, and comprising less than 1000 ppm of carbon content, wherein the particles have a particle size distribution (PSD) of 20 nm to 350 nm.

[013] As embodied and broadly described herein, the present disclosure relates to a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the composition comprising metal-based spherical particles doped with a doping agent
25 that operates to increase the sintering temperature of the composition, and comprising less than 1000 ppm of carbon content, wherein the particles have a particle size distribution (PSD) of 20 nm to 300 nm, with particles having a size > 350 nm representing less than 1 ppm.

[014] As embodied and broadly described herein, the present disclosure relates to a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the composition comprising metal-based spherical particles doped with a doping agent
30

5 that operates to increase the sintering temperature of the composition, and comprising less than 1000 ppm of carbon content, wherein the particles have a $D_{99} \leq 250$ nm.

[015] As embodied and broadly described herein, the present disclosure relates to a multilayer ceramic capacitor (MLCC) comprising a plurality of dielectric layers and electrode layers arranged to form a stack where the dielectric layers and the electrode layers alternate, one or
10 more of the electrode layers being formed from a precursor layer including the composition as described herein.

[016] As embodied and broadly described herein, the present disclosure relates to a process for obtaining a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the process comprising providing metal-based particles doped with a doping
15 agent that operates to increase the sintering temperature of the composition, vaporizing the metal-based particles to obtain the metal and doping agent in vapor form and cooling the metal and doping agent in vapor form so as to obtain the composition in particulate form for use in the MLCC wherein the composition comprises less than 1000 ppm of carbon content, and wherein the particles have a median size (D_{50}) of ≤ 120 nm.

[017] As embodied and broadly described herein, the present disclosure relates to a process for obtaining a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the process comprising providing metal-based particles doped with a doping
20 agent that operates to increase the sintering temperature of the composition, vaporizing the metal-based particles to obtain the metal and doping agent in vapor form and cooling the metal and doping agent in vapor form so as to obtain the composition in particulate form for use in the MLCC
25 wherein the composition comprises less than 1000 ppm of carbon content, and wherein the particles have a particle size distribution (PSD) of 20 nm to 350 nm and a D_{90} of ≤ 200 nm.

[018] As embodied and broadly described herein, the present disclosure relates to a process for obtaining a composition in particulate form for use in an electrode layer of a multilayer ceramic
30 capacitor (MLCC), the process comprising providing metal-based particles doped with a doping agent that operates to increase the sintering temperature of the composition, vaporizing the metal-based particles to obtain the metal and doping agent in vapor form and cooling the metal and doping agent in vapor form so as to obtain the composition in particulate form for use in the MLCC

5 wherein the composition comprises particles having a particle size distribution (PSD) of 20 nm to 300 nm, with particles having a size > 350 nm representing less than 1 ppm.

[019] As embodied and broadly described herein, the present disclosure relates to a process for obtaining a composition in particulate form for use in an electrode layer of a multilayer ceramic capacitor (MLCC), the process comprising providing metal-based precursor particles doped with
10 a doping agent that operates to increase the sintering temperature of the composition, vaporizing the metal-based precursor particles to obtain the metal and doping agent in vapor form and cooling the metal and doping agent in vapor form so as to obtain the composition in particulate form for use in the MLCC wherein the composition comprises less than 1000 ppm of carbon content and particles having a $D_{99} \leq 250$ nm.

15 [020] As embodied and broadly described herein, the present disclosure relates to a process for providing the metal-based precursor particles doped with the doping agent as described herein, comprising mixing the doping agent with molten metal to obtain a molten metal-doping agent mixture; and atomizing the mixture to obtain the metal-based precursor particles doped with the doping agent.

20 [020a] As embodied and broadly described herein, the present disclosure relates to a process for producing doped metallic nanoparticles, the process comprising the steps of preparing metallic microparticles comprising mixing a liquid doping agent with metal at a temperature sufficient to react the doping agent with the metal and heating to a temperature to melt the metal to obtain a molten metal-doping agent mixture; and obtaining metallic microparticles by atomization of the
25 molten metal-doping agent mixture, wherein the metallic microparticles have the doping agent distributed therein; and preparing metallic nanoparticles comprising evaporating the metallic microparticles to produce a metallic vapor; and cooling the metallic vapor; wherein cooling of the metallic vapor condensates the metal and the doping agent to produce the doped metallic nanoparticles.

30 [020b] As embodied and broadly described herein, the present disclosure relates to a system for producing doped metallic nanoparticles, comprising a first atomization unit for preparing

5 metallic microparticles comprising a first unit for mixing a liquid doping agent with metal at a temperature sufficient to react the doping agent with the metal and heating to a temperature to melt the metal to obtain a molten metal-doping agent mixture; and a second unit in fluid communication with the first unit, the second unit being configured for obtaining metallic microparticles by atomization of the molten metal-doping agent mixture, wherein the metallic microparticles have the doping agent distributed therein; and a second atomization unit for preparing metallic nanoparticles comprising a first unit for receiving and evaporating the metallic microparticles to produce a metallic vapor; and a second unit in fluid communication with the first unit, the second unit being configured for receiving and cooling the metallic vapor; wherein cooling of the metallic vapor condensates the metal and the doping agent to produce the doped metallic nanoparticles.

15 [021] All features of exemplary embodiments which are described in this disclosure and are not mutually exclusive can be combined with one another. Elements of one embodiment can be utilized in the other embodiments without further mention. Other aspects and features of the present technology will become apparent to those ordinarily skilled in the art upon review of the following description of specific embodiments in conjunction with the accompanying drawings.

20 **BRIEF DESCRIPTION OF THE DRAWINGS**

A detailed description of specific embodiments is provided herein below with reference to the accompanying drawings in which:

[022] Fig. 1 is a flowchart illustrating a process for manufacturing a composition for use in a multi-layer ceramic capacitor (MLCC) in accordance with an embodiment of the present disclosure;

- 5 [024] Fig. 2 is a flowchart illustrating a process for obtaining metal-based precursor particles for use in the process of Fig. 1 in accordance with an embodiment of the present disclosure;
- [025] Fig. 3 is a flowchart illustrating a process implementing the processes of Fig. 1 and Fig. 2 for obtaining nickel-based particles doped with sulfur in accordance with an embodiment
10 of the present disclosure;
- [026] Fig. 4 is a scanning electronic microscope image of a composition comprising nickel-based particles obtained with the process of Fig. 1;
- [027] Fig. 5A, 5B and 5C are scanning electronic microscope (SEM) images of a composition comprising nickel-based particles obtained with the process of Fig. 1, before
15 classification;
- [028] Fig. 6 is a schematic representation of a MLCC in accordance with an embodiment of the present disclosure;
- [029] Fig. 7 is a cross section of the MLCC of Fig. 6 in accordance with an embodiment of the present disclosure;
- 20 [030] Fig. 8 is a schematic representation of a cross section of the MLCC of Fig. 6 including an internal electrode layer and dielectric layers, before a sintering process, in accordance with an embodiment of the present disclosure;
- [031] Fig. 9A is a schematic representation of the cross section of the MLCC of Fig. 8 after the sintering process, in accordance with an embodiment of the present disclosure;
- 25 [032] Fig. 9B is a schematic representation of typical scanning electronic microscope (SEM) images that can be obtained from a cross section of the MLCC of Fig. 9A, in accordance with an embodiment of the present disclosure;
- [033] Fig. 10 is a schematic representation of the cross section of the MLCC of Fig. 8 where the electrode layer includes fine contaminant particles, in accordance with an embodiment
30 of the present disclosure;

- 5 [034] Fig. 11 is a schematic representation of the cross section of the MLCC of Fig. 10, after the sintering process, in accordance with an embodiment of the present disclosure;
- [035] Fig. 12 is a schematic representation of the cross section of the MLCC of Fig. 10, after the sintering process, comprising undesirable compounds, in accordance with an embodiment of the present disclosure;
- 10 [036] Fig. 13A is a first schematic representation of the cross section of the MLCC of Fig. 8, after the sintering process, comprising a cracked MLCC, in accordance with an embodiment of the present disclosure;
- [037] Fig. 13B is a second schematic representation of the cross section of the MLCC of Fig. 8, after the sintering process, comprising a cracked MLCC, in accordance with an
15 embodiment of the present disclosure;
- [038] Fig. 14 is a schematic representation of a typical scanning electronic microscope (SEM) image of a metal-based particle showing an oxidation layer on its surface in accordance with an embodiment of the present disclosure;
- [039] Fig. 15 is a graph illustrating the sintering behavior of nickel-based particles doped with sulfur compared to nickel-based particles without a doping agent, in accordance with an
20 embodiment of the present disclosure;
- [040] Fig. 16A is a scanning electronic microscope (SEM) image of a composition comprising nickel-based precursor particles doped with sulfur classified to retain fine sizes in accordance with an embodiment of the present disclosure;
- 25 [041] Fig. 16B is a scanning electronic microscope (SEM) image of a composition comprising nickel-based precursor particles doped with sulfur classified to retain coarse sizes in accordance with an embodiment of the present disclosure;
- [042] Fig. 17 is a graph illustrating particle size distribution of nickel-based particles doped with sulfur and classified to obtain a D50 of 80 nm, in accordance with an embodiment of the
30 present disclosure;

5 [043] In the drawings, exemplary embodiments are illustrated by way of example. It is to be expressly understood that the description and drawings are only for the purpose of illustrating certain embodiments and are an aid for understanding. They are not intended to be a definition of the limits of the invention.

DETAILED DISCLOSURE

10 [044] The present technology is explained in greater detail below. This description is not intended to be a detailed catalog of all the different ways in which the technology may be implemented, or all the features that may be added to the instant technology. For example, features illustrated with respect to one embodiment may be incorporated into other embodiments, and features illustrated with respect to a particular embodiment may be deleted from that
15 embodiment. In addition, numerous variations and additions to the various embodiments suggested herein will be apparent to those skilled in the art in light of the instant disclosure which variations and additions do not depart from the present technology. Hence, the following description is intended to illustrate some particular embodiments of the technology, and not to exhaustively specify all permutations, combinations and variations thereof.

20 [045] The present inventors have through extensive R&D work developed and designed compositions in particulate form for use as electrode material in multilayer ceramic capacitors (MLCCs) and a method of manufacturing same, where the compositions include particles having nanometric sizes that are more suitable to the increasing demands of the industry. Indeed, since the capacitance of a MLCC is dependent to the number of laminated layers and the thickness of
25 the dielectric layer, it is advantageous to ensure that the MLCC be as thin as possible. This is where using the compositions in particulate form described herein in the manufacturing of the electrode layer disposed between dielectric layers can be advantageous in that these compositions have particles of smaller size with reduced coarse particles content than what has been known in the art so far.

30 [046] The compositions described herein also have reduced content of contaminants, such as carbon, which can result in better electrochemical performances of MLCCs and/or which can result in less delamination or cracks during the manufacturing of MLCCs. Indeed, typically, during manufacturing of MLCC, carbon on the surface of metal-based particles may be removed

5 during a “bake-out” step at a temperature exceeding 200 °C, where excessive amounts of carbon
can cause delamination and cracks in the MLCC. Such delamination and cracks are undesirable
and their presence will typically cause the rejection of the MLCC, thus, reducing manufacturing
productivity. Additionally or alternatively, when carbon is present inside the metal-based
particles, the carbon may not be easily removed even through the above-mentioned “bake-out”
10 step, thus, remaining in the MLCC. Without being bound by any theory, it is believed that this
residual carbon may also cause deficiencies in the MLCC in terms of long term reliability, such
for example, with respect to capacitance, DC bias, reliability, and the like.

Compositions characteristics

[047] In a broad non-limiting aspect, the compositions in particulate form for use in
15 MLCCs of the present disclosure have metal-based particles, where the metal can be selected
from silver, copper, lead, palladium, platinum, nickel, gold, cobalt, iron, cadmium, zirconium,
molybdenum, rhodium, ruthenium, tantalum, titanium, tungsten, zirconium, niobium, and the
like, as well as from alloys thereof. During the manufacturing of MLCCs, these compositions
can be used as powders (i.e., in particulate form) or as slurry / pastes. Such slurry / pastes include
20 binders suitable for the purpose of making electrodes in MLCCs, which are known in the art and,
for conciseness sake, will not be further described here.

[048] In some specific implementations, the metal-based particles of the present disclosure
can also be doped with a doping agent, which operates to increase the sintering temperature of
the metal-based particles during manufacture of the MLCC. During the manufacturing of
25 MLCCs, typically, there is a sintering step where the electrode materials and dielectric ceramic
materials are heated to temperatures which can reach up to about 1500 °C for a sufficient time
period resulting in densification of the electrode materials and dielectric ceramic materials and
achieving desirable conductivity properties. When these materials include particles, the sintering
step will cause fusion at contact points between adjacent particles. Typically, metals used in the
30 electrode materials have a significantly lower sintering temperature than that one of ceramic
materials such that without the presence of at least a doping, which operates to increase the
sintering temperature of the metal-based particles, there will be large differences in terms of
respective sintering onset temperatures, which may result in microstructures and/or by-products

5 that may negatively impact the MLCC and/or cause an increase in manufacturing rejections. For example, when using nickel-based particles as electrode material and BaTiO₃ as ceramic material, the sintering onset temperature for pure nickel being about 150 °C and the sintering onset temperature for BaTiO₃ to obtain desirable dielectric properties required for use in MLCCs being typically > 1000 °C, there is a significant sintering onset temperature gap that one must
10 avoid. This is an example where the presence of a doping agent, which operates to increase the sintering temperature of the metal-based particles during manufacture of the MLCCs, is advantageous.

[049] The doping agent can be a single material or a blend of different materials. For example, the doping agent can operate to increase the onset temperature (beginning of sintering)
15 and/or increase the sintering offset temperature (end of sintering). In a specific example of implementation, the amount of doping agent and/or the nature of the doping agent is selected such that the onset temperature (beginning of sintering) and/or the sintering offset temperature (end of sintering) of the metal-based particles sufficiently overlaps with the sintering temperature range of the ceramic materials.

[050] In some embodiments, the doping agent can be homogeneously distributed in the
20 metal-based particles and/or at the surface of the particles. In other embodiments, the doping agent can be heterogeneously distributed in the metal-based particles and/or at the surface of the particles. In yet other embodiments, the doping agent can be homogeneously distributed in the metal-based particles and heterogeneously distributed at the surface of the particles. In yet other
25 embodiments, the doping agent can be heterogeneously distributed in the metal-based particles and homogeneously distributed at the surface of the particles.

[051] In some specific implementations, the doping agent is a high melting point metal. Examples of high melting point metal, include, but are not limited to chromium, vanadium, titanium, zirconium, niobium, tantalum, platinum, boron, ruthenium, molybdenum, tungsten,
30 rhodium, iridium, osmium, rhenium, and their alloys or mixtures thereof. In some other embodiments, the doping agent is a metal with a melting point higher than the melting point of nickel. In some embodiments, the high melting point metal is an oxide or a salt.

[052] In some specific implementations, the doping agent is sulfur.

- 5 [053] In some specific implementations, the doping agent in the metal-based particles includes from 0.01 to 0.5 wt.% of sulfur content.
- [054] In some specific implementations, the compositions of the present disclosure include nickel-based particles doped with sulfur.
- [055] In some specific implementations, the compositions of the present disclosure are
10 prepared according to a process that controls the carbon content, such that compositions include < 1200 ppm. For example, the compositions of the present disclosure can include < 1000 ppm, < 900 ppm, < 800 ppm, < 700 ppm, < 600 ppm, < 500 ppm, < 400 ppm, < 300 ppm, < 200, or < 100 ppm of carbon content.
- [056] In some specific implementations, the compositions of the present disclosure are
15 prepared according to a process that controls the oxygen content in the particles to obtain satisfactory electrochemical performance of the MLCC.
- [057] The presence of an oxidation layer on the surface of the herein described metal-based particles can also positively modify dispersion and/or flowability properties of the compositions in particulate form.
- 20 [058] In some specific implementations, the compositions of the present disclosure are prepared according to a process that controls the oxygen content in the particles to up to 5 wt.% oxygen content. For example, from 0.1 wt.% to 5 wt.%, 0.1 wt.% to 3.5 wt.%, 0.1 wt.% to 2.0 wt.%, 0.1 wt.% to 1.5 wt.%, 0.1 wt.% to 0.6 wt.%, 0.2 wt.% to 5 wt.%, 0.2 wt.% to 3.5 wt.%, 0.2 wt.% to 2.0 wt.%, 0.2 wt.% to 1.5 wt.%, 0.2 wt.% to 0.6 wt.% oxygen content.
- 25 [059] Without being bound by any theory, the present inventors believe that control over the oxygen content can be beneficial for a number of reasons. For example, when the metal-based particles are nickel-based particles, if the nickel electrode is oxidized over a threshold level, this will cause the presence of structural defects by volume expansion during the MLCC manufacturing process. That is, when Ni is changed into NiO, unit cell volume increases by
30 169%. However, when the oxygen content is mainly contained in a surface layer disposed on the metal-based particles, it results in an improvement in the stability and thermal behavior of the metal.

5 [060] In some specific implementations, the compositions of the present disclosure include metal-based particles that include an oxidation layer on at least a portion of the particle surface. In some embodiments, the oxidation layer completely covers the particle surface. For example, the main portion or all of the oxygen content discussed previously may be included the oxidation layer. In some embodiments, the oxidation layer has a thickness of less than 15 nm. For example,
10 the oxidation layer can have a thickness of from 2 nm to 10 nm, or from 2 nm to 5 nm, such as for example a 3 nm or 4 nm oxidation layer. The person of skill will readily understand that the thickness of the oxidation layer may be an average thickness in that it may vary in thickness along the surface of the metal-based particle. Accordingly, the thickness may be an average thickness value as measured by electron microscopy techniques.

15 [061] In some embodiments, when the metal-based particles are nickel-based particles doped with sulfur, the oxidation layer can include nickel oxide and nickel sulfide.

[062] In some specific implementations, the compositions of the present disclosure include metal-based particles that have nanometric sizes. For example, the composition may include particles having a particle size distribution (PSD) of 15 nm to 350 nm (prior to classification) or
20 a PSD of 20 nm to 350 nm (after classification). Such PSD is, contrary to what is obtained with known processes in the art, tightly controlled such that, for example, the particles have sizes that are skewed towards smaller sizes instead of having sizes skewed towards coarser sizes. There are clear technical benefits in obtaining such sizes (as discussed previously in this text) as well as economic benefits: when the composition in particulate form coming out of the manufacturing
25 process has less coarse sizes, there is less wasted material (material which would not make the cut-off classification values) and as such, yields are increased.

[063] For example, the composition may include one or more of the following particle size features:

- PSD of 20 nm to 350 nm, or 20 nm to 300 nm, or 20 nm to 200 nm;
- 30 • $D_{90} \leq 200$ nm, or $D_{90} \leq 150$ nm, $D_{90} \leq 130$ nm;
- median size (D50) of ≤ 120 nm, or median size (D50) of ≤ 100 nm, or median size (D50) of ≤ 80 nm, or median size (D50) of ≤ 50 nm;

- 5
- particles having a size > 350 nm representing less than 1 ppm;
 - $D_{99} \leq 250$ nm, or $D_{99} \leq 230$ nm;
 - less than 3 particles having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition, or less than 2 particles having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition, or 1 or no particle having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition;
- 10
- less than 3 particles having a size > 650 nm in a scanning electronic microscope image of 5000x of the composition, or less than 2 particles having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition, or 1 or no particle having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition
- 15
- less than 3 particles having a size > 350 nm in a scanning electronic microscope image of 5000x of the composition, or less than 2 particles having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition, or 1 or no particle having a size > 1 μm as determined from a scanning electronic microscope (SEM) image of 5000x of the composition.
- 20

[064] The person of skill will appreciate that the SEM image is an image of a predetermined area of the composition being analyzed, which will vary depending on at least the D50 of the composition to ensure accuracy and/or statistical significance. For example, a D50 of 120 nm can require a 5 μm per 5 μm area, whereas a D50 of 80 nm can require a 3 μm per 3 μm area and a D50 of 50 nm can require a 2 μm per 2 μm area of the composition.

25

[065] Particle size features of a composition in particulate form can be determined using techniques well known in the art, such as, but not limited to, laser diffraction spectroscopy, transmission electron microscopy, scanning electron microscopy (SEM), and the like. Such techniques are well known and for conciseness sake, will not be further described here.

30

5 Multilayer ceramic capacitor (MLCC)

[066] In a broad non-limiting aspect, the compositions in particulate form described herein allow one to manufacture MLCCs having advantageous properties. MLCCs typically include a ceramic body including dielectric layers. MLCCs also include a plurality of internal electrode layers disposed within the ceramic body, having at least one of the dielectric layers interposed there between, stacked along a thickness direction, being parallel with respect to an external surface, such as a mounting surface.

[067] Fig. 6 and Fig. 7 illustrate MLCC **270** including a plurality of dielectric layers **274** in accordance with an embodiment of the present disclosure. The dielectric layers **274** may include a ceramic material having high permittivity, for example, a composition including barium titanate (BaTiO₃)-based particles or strontium titanate (SrTiO₃)-based particles. MLCC **270** includes a plurality of internal electrodes **276**, where each internal electrode **276** is disposed between two dielectric layers **274** which comprise ceramic material **284** (as shown in Fig. 8). The internal electrodes **276** are made using a composition **230** comprising metal-based particles **240**. Fig. 8 shows a plurality of particles **240** before sintering. Fig. 9A illustrates the MLCC **270** of Fig. 8, but after sintering, where the particles **240** of composition **230** have fused at contact points between the particles, partially deforming to the point of not being perfectly spherical any more, as best shown in the picture illustrated in Fig. 9B. The person of skill will readily realize that the composition **230** can take the form of a slurry / paste which is spread on the surface of the dielectric layers **274**, which slurry / paste may include a number of additional ingredients such as organic solvent(s) and binder resin(s).

[068] Typically, the capacitance of a MLCC is dependent to the number of laminated layers and to the thickness of the dielectric layer, and as such, it is advantageous to ensure that the MLCC be as thin as possible. This is where using the composition in particulate form described herein in the manufacturing of the electrode layers disposed between dielectric layers can be advantageous in that this composition has particles of smaller size with reduced coarse particles content than what has been known in the art so far, thus, allowing one to reduce the overall thickness of MLCCs.

5 [069] For example, when using the composition of the present disclosure, one can manufacture a MLCC where on a cross section **7A** of the ceramic body in a direction perpendicular to the mounting surface, as shown for example in Fig. 6 and Fig. 7, two adjacent dielectric layers **274** separated by an internal electrode layer **276** can have an average distance d of < 800 nm between respective points intersecting an axis **290** perpendicular to the mounting
10 surface. This distance d can be for example < 500 nm, < 400 nm, < 300 nm, or a distance of > 100 nm. This distance d is shown in Fig. 9B.

[070] In order to manufacture standardized MLCCs, each internal electrode **276** as illustrated in Figs. 9A and 9B requires a certain average number of particles **240** to allow the internal electrodes **276** to have relatively uniform thickness, which is advantageously as thin as
15 possible. The average number of particles **240** of internal electrode **276** may be assessed in a number of ways. For example, one can dissect the MLCC along axes **7A** as shown in Fig. 6 to obtain a cross section of the ceramic body in a direction perpendicular to the external surface as shown in Fig. 7. In this cross section, one can determine the number of particles **240** in a number of electrodes **276** over a pre-determined number (e.g., 25, 36, 64, etc.) of locations which cross
20 axis **290** which is perpendicular to the plurality of electrodes **276** as shown in Fig. 7 and averaging the obtained values. The composition in particulate form of the present disclosure has a particle size distribution such that an electrode layer interposed between two adjacent dielectric layers prior to a sintering process includes from 2 to 8 metal-based spherical particles disposed in a direction parallel to the axis **290**, such as from 3 to 5 metal-based spherical particles.

25 [071] If the average number of particles **240** in a given electrode layer **276** throughout various locations crossing respective axes **290** is not consistent throughout, e.g., the standard deviation is too high, some portions of the given internal electrode **276** will significantly be thicker than other portions, which may translate into inconsistent electrical properties and/or out-of-spec MLCC. At least for this reason, the herein described composition in particulate form
30 having the previously discussed size features is advantageous – in the present invention, there is clearly more control over the particle size features and, thus, less variability in terms of electrical properties and thickness of MLCC. This control over the particle size features thus may result in less out-of-spec MLCC, thus, reducing defective fractions in production batches and increasing productivity.

5 [072] The person of skill will readily understand that the metal-based particles will not
retain the spherical shape after sintering (as shown in Fig. 9B), since the particles are somewhat
deformed due to material fusion and compression at the contact points between the particles.
Nevertheless, after sintering, the particles are still recognizable as more or less discrete particles
and one can typically still assess the number of particles disposed in a direction parallel to the
10 cross section.

Process of manufacture of the composition

[073] In a broad non-limiting aspect, the compositions in particulate form described herein
can be manufactured using a process that vaporizes precursor materials so as to obtain a gas
containing the precursors in vapor form. The present inventors have developed a process which
15 allows one to control the residence time of the precursor materials in the vaporization zone so as
to sufficiently vaporize the precursors to ensure that there are no remaining precursors in solid
form after the manufacturing process, which can be undesirable in particular when such
precursors include particles in micron size that would find their way into the composition in
particulate form and thus skew its PSD towards coarser sizes.

20 [074] The present inventors have also developed a way to control the cooling rate of the
gas containing the precursors in vapor form so as to obtain a herein described composition in
particulate form having the desired particle size features discussed previously.

[075] Fig. 1 illustrates a process **20** for manufacturing a composition in particulate form
described herein in accordance with an embodiment of the present disclosure. The process **20**
25 includes step **22** of evaporating precursor materials (e.g., metal and doping agent) to obtain a gas
containing the precursor materials in vapor form. For example, step **22** may be implemented
using an inductively coupled plasma torch (ICP torch) (e.g., TEKNA PL-50, PN-50, PL-35, PN-
35, PL-70, PN-70, PN-100) or a direct current (DC) plasma torch (e.g., those commercialized by
Praxair, Oerlikon-Metco, Pyrogenesis or Northwest Mettech).

30 [076] Advantageously, the process **20** is designed so as to optimize the residence time of
the precursor materials into the plasma reaction zone of the torch to cause sufficient evaporation
of the precursor materials to ensure that there are no precursor materials in solid form entrained

5 in the gas containing the precursor materials in vapor form. For example, when the process 20 is implemented in an ICP torch, precursor materials in solid form entrained in the gas containing the precursor materials in vapor form could interfere with the desired PSD and result in particles having coarse particle sizes.

[077] In some embodiments, the residence time of the precursor materials into the plasma
10 reaction zone of the torch may be controlled and optimized by controlling the precursor materials feeding rate into the plasma reaction zone. In some embodiments, the precursor materials feeding rate may be controlled through controlling operational parameters for the feeding device, such as motor RPM if it is a rotating distribution device, vibration parameters if it is a vibration motor device, and the like. For example, the present inventors have discovered that a feeding rate in the
15 range of 10 to 35 g/min of precursor materials in particle form through a ¼ inch feeding tube which is consistent in time (not varying in time by more than 1%) affords best results with an ICP torch.

[078] The present inventors have also discovered that while using a carrier gas to transport precursor materials from the feeding inlet into the plasma reaction zone at more or less high
20 speeds can be useful to prevent settlement within the transport circuit and thus prevent clogging of the system, a carrier gas flow rate which is too high results in particle speeds which are also too high, thus, reducing residence time of the precursor materials into the plasma reaction zone. For example, the present inventors have discovered that a flow rate of carrier gas at a consistent (i.e., not varying in time by more than 1%) flow rate ≤ 10 L/min in a feeding tube of a ¼ inch
25 inner diameter. The carrier gas flow rate can be manually controlled or using a computerized system.

[079] In some embodiments, an additive gas (e.g., oxygen) can be incorporated in a controlled manner into the process so as to obtain from 0.1 wt.% to 5 wt.% oxygen content in the metal-based particles. For example, the additive gas (e.g., oxygen) can cause formation of an
30 oxide layer on the surface of particles having a thickness of less than 15 nm, such as less than 10 nm, less than 5 nm, such as 2 to 4 nm. The additive gas (e.g., oxygen) can have a consistent (i.e., not varying in time by more than 1%) flow rate so as to obtain such oxygen content and/or oxidative layer. For example, the additive gas flow rate can be in the range of 0.5 to 1.5 L/min.

5 [080] There are several ways of obtaining the precursor materials used in step 22. One embodiment will now be discussed with reference to Fig. 2.

[081] Fig. 2 outlines an atomization process 10, which can be used for obtaining metal-based precursor particles doped with the doping agent in accordance with an embodiment of the present disclosure. Atomization processes are known in the art, such as gas atomization, DC plasma
10 atomization, inductively coupled plasma atomization, and the like, and as such, details of the systems used to implement the atomization process 10 will not be described in great detail here.

[082] The atomization process 10 includes a step 12 of dissolving the doping agent in molten metal to obtain a molten metal/doping agent mixture. For example, in one embodiment, the step 12 may include mixing liquid doping agent with metal at a temperature sufficient to react the
15 doping agent with the metal and heating to a temperature to melt the metal to obtain a molten metal-doping agent mixture. As discussed previously, the doping agent may be a single doping agent or a blend of doping agents. Optionally, the process 10 may include a step (not shown) of assessing a concentration of doping agent present in the molten metal/doping agent mixture and, if necessary, adjusting the concentration of doping agent to compensate for any loss of doping
20 agent through, for example, volatilization caused by the high melting temperatures used to obtain the mixture. The doping agent concentration in the mixture is controlled so as to obtain metal-based precursor particles doped with, for example, from 0.01 to 0.5 wt.% of doping agent.

[083] The molten metal/doping agent mixture is then atomized at a step 14 to form metal-based precursor particles doped with the doping agent. Typically, the precursor particles obtained
25 at this step will have a PSD including micron sizes. Typically, the metal-based precursor particles obtained with atomization process 10 are substantially spherical. In other words, the particles have a degree of deviation from perfect spherical shape that is sufficiently small so as to not measurably detract therefrom. The exact degree of deviation allowable may in some cases depend on the specific context.

[084] The process 10 may then include a sieving (e.g., using sieving membranes, or mesh or
30 cloth) or gas-classification step 16 to retain a particle size distribution of interest. In some instances, an inert gas classification system can be used to obtain the desired particle size

5 distribution. In some embodiments, the metal-based precursor particles doped with the doping agent have a particle size distribution (PSD) of from 1 μm to 200 μm , or any PSD within such

5 range. In some embodiments, the metal-based precursor particles doped with the doping agent have an average median (D50) size in the range of from 1 μm to 25 μm , or from 1 μm to 15 μm , or from 1 μm to 10 μm , or from 5 μm to 25 μm , or from 5 μm to 15 μm , or from 5 μm to 10 μm , and the like. In some embodiments, the metal-based precursor particles doped with the doping agent have a D90 particle size distribution < 50 μm , or < 45 μm , or < 40 μm , or < 35 μm , or < 30
10 μm , or < 25 μm and the like. In some embodiment, the metal-based precursor particles doped with the doping agent have a specific surface area (SSA) as measured by the Brunauer-Emmett-Teller adsorption method (BET) that is at least 0.15 m^2/g , or at least 0.20 m^2/g , or at least 0.25 m^2/g , and the like. Techniques for sieving (e.g., using sieving membranes, or mesh or cloth) or gas-classification are well known in the art, and as such, will not be further described here.

15 [085] In some specific implementations, the process **10** is implemented in a system that does not make use of graphite-containing elements in zones of high heat so as to minimize contamination of the metal-based precursor particles with high contents of carbon. For example, the metal-based precursor particles produced with the atomization process **10** will contain less than 1200 ppm, or less than 1000 ppm, or less than 900 ppm, or less than 800 ppm, or less than 700
20 ppm, or less than 600 ppm, or less than 500 ppm, or less than 400 ppm, or less than 300 ppm, or less than 200 ppm of carbon content. Examples of suitable atomization systems for implementing such process are described, for example, in any one of U.S. Pat. No: 9,718, 131; U.S. Pat. No: 5,707,419; WO 2011/054113, WO 2017/011900, WO 2017/070779; WO 2017/177315; and WO 2016/191854.

25 [086] In some embodiment, the metal-based precursor particles produced with the atomization process **10** will contain from 0.1 wt.% to 5 wt.% oxygen content, such as up to 3.5 wt.%, up to 2.0 wt.%, up to 1.5 wt.%, up to 0.6 wt.%, and the like.

[087] In some embodiment, the metal-based precursor particles produced with the atomization process **10** are substantially pure. In other words, the metal-based precursor particles
30 do not include significant undesired components levels, such as < 0.5 wt.%, < 1 wt.%, < 2 wt.%, < 3 wt.%, < 4 wt.%, < 5 wt.%, < 6 wt.%, < 7 wt.%, < 8 wt.%, < 9 wt.% or < 10wt. % undesired components.

5 [088] As the person of skill will readily understand, the process **10** advantageously produces metal-based particles which are used as carriers for the doping agent.

[089] Returning to Fig. 1, the process **20** for manufacturing the composition in particulate form includes a step **24** of cooling the gas containing the precursor materials in vapor form so as to cause the metal and doping agent to recombine and obtain a composition in particulate form.
10 For instance, in some examples, a cooling rate may be controlled such as to obtain the metal-based particles of the present disclosure. In some instances, the cooling rate may be controlled such that the gas temperatures are reduced to below about 350°C. In some instances, vaporized metal and doping agent are cooled down in a controlled manner using a quench gas having a consistent (i.e., not varying in time by more than 1%) flow rate so as to obtain the desired particle size distribution.
15 For example, the quench gas can be incorporated into the process at a consistent flow rate in the range of 1000 to 8000 L/min so as to obtain the desired particle size distribution.

[090] The process **20** may also include a classification step (not show) to discard particles having a size < 20 nm such as particles **248** illustrated in Fig. 10. For example, CA 2,912,282 describes that powder particles can be recovered from an atomization process, for example in a
20 downstream cyclone or in a filter, depending on their particle size distribution where the cyclone is a well-known device to perform size classification as described in Yoshida et al., J. of chemical engineering of Japan, 1991 Volume 24 Issue 5 Pages 640-647, for example using a gas such as air. In one embodiment, therefore, the classification described herein is a gas-classification and can be performed with a cyclone. Without being bound by any theory, the presence of particles **248** may
25 be problematic in that their presence may interfere with additives that are typically added to the electrode material slurry / paste when manufacturing MLCC, such as BaTiO₃ which typically also have a size < 20 nm. In other words, when manufacturing MLCC, it is desirable to have the additives fill void spaces between particles **240** and as such, it is desirable to reduce as possible the content of other particles of similar size which would prevent these additives from occupying
30 these void spaces. Alternatively or additionally, and again without being bound by any theory, presence of particles **248** having a size < 20 nm in the composition **230** may be detrimental during the sintering step in that these may chemically react with other elements causing a presence of undesirable compounds **290** into the internal electrodes **276** as shown in Fig. 12, and/or fuse with adjacent particles **240** (e.g. about a fused area between metal-based particles **240**) as shown in Fig.

- 5 11, thereby altering the microstructure of the internal electrodes **276**, harming the electric properties of the internal electrodes **276**, and/or diminishing the quality of the internal electrode **276** after sintering.

5 [091] The process **20** thus offers clear advantages in preparing MLCC with reduced likelihood of rejections. As discussed previously, the process **20** reduces contaminant contents, such as carbon (to levels such as < 1000 ppm), which when present in sufficiently high levels (> 1400 ppm) in the composition **230**, may induce the presence of cracks **290**, as illustrated in Fig. 13A and shown in Fig. 13B, which increases rejection of MLCC.

10

Definitions

[092] Unless otherwise defined, all technical and scientific terms used herein have the same meaning as commonly understood by a person of ordinary skill in the art to which the present invention pertains. As used herein, and unless stated otherwise or required otherwise by
15 context, each of the following terms shall have the definition set forth below.

[093] As used herein, the term “dopant” and the expression “doping agent” are used interchangeably and refer to a trace impurity elements that is inserted into a substance (in very low concentrations) to modify the thermodynamic and/or electrical and/or optical properties of the substance.

20 [094] As used herein, the term “alloy” refers to a mixture of metals or a mixture of a metal and another element. Alloys are defined by a metallic bonding character. An alloy may be a solid solution of metal elements (a single phase) or a mixture of metallic phases (two or more solutions). Intermetallic compounds are alloys with a defined stoichiometry and crystal structure.

[095] As used herein, the term “plasma” refers to a state of matter in which an ionized
25 gaseous substance becomes highly electrically conductive to the point that long-range electric and magnetic fields dominate the behavior of the matter. Plasma is typically artificially generated by heating neutral gases or by subjecting that gas to a strong electromagnetic field.

[096] The expressions “plasma torch”, “plasma arc”, “plasma gun” and “plasma cutter” are used herein interchangeably and refer to a device for generating a direct flow of plasma.

30 [097] As used herein, the abbreviation “ μm ” designates micrometers and the abbreviation “nm” designates nanometers.

5 [098] As used herein, the expression “particle size distribution” or “PSD” defines the relative amount of particles present according to size. The way PSD is determined in the present disclosure is with either laser diffraction spectroscopy and/or field emission gun scanning electron microscopy (FEG-SEM), where powder is separated on sieves of different sizes. For example, D90 = 150 nm indicates that 90% of the particles have a size which is smaller than 150
10 nm.

EXAMPLES

[099] The examples below are given so as to illustrate the practice of various embodiments of the present disclosure. They are not intended to limit or define the entire scope of this disclosure. It should be appreciated that the disclosure is not limited to the particular
15 embodiments described and illustrated herein but includes all modifications and variations falling within the scope of the disclosure as defined in the appended embodiments.

Example 1

[100] In this example, a composition comprising nickel-based precursor particles doped with sulfur was prepared in accordance with an embodiment of the present disclosure.

20 [101] Briefly, a nickel source and sulfur source were loaded in a furnace and heated to the melting temperatures of sulfur (115-440 °C). The temperature was held for sufficient time to allow reaction of liquid sulfur with nickel to form NiS or Ni₃S₂. When the reaction was deemed complete, i.e., all sulfur was converted in the form of NiS, the temperature was raised to the melting temperature of nickel (1400-1500 °C) to obtain a melted mixture. The melted mixture
25 was then gas-atomized to obtain a composition comprising nickel-based precursor particles doped with 0.01 to 0.5 wt.% of sulfur content. The process was repeated three times and the results are reproduced in the Table 1, where the composition obtained in process #3 was sieved into fine and coarse particle sub-fractions.

[102] All compositions were analyzed by LECO analysis to determine O, C, N and H
30 contents and by laser diffraction spectroscopy to determine particle size distribution features.

Table 1

Process #	S content wt.%	PSD (μm)			O wt.%	C wt.%	N wt.%	H wt.%
		D10	D50	D90				
1	0.280	25.7	62.1	103	1.1	0.082	na	na
2	0.320	14.5	40.4	104	1.5	0.280	na	na
3 (fine)	0.033	6.6	14.3	43.2	0.55	0.012	na	na
3 (coarse)	0.020	22.5	52.7	108.8	0.50	0.005	na	na

5

Example 2

[103] In this example, a composition comprising nickel-based particles doped with sulfur was prepared in accordance with an embodiment of the present disclosure.

[104] Briefly, a composition comprising nickel-based precursor particles doped with 0.01 to 0.5 wt.% of sulfur having a particle size distribution from 10 μm to 100 μm was vaporized in an ICP torch (PN50, Tekna Plasma Systems, Inc.) at a power in the range of 60 to 80 kW under reducing plasma conditions (argon / hydrogen). A scanning electronic microscope (SEM) image was obtained from a sample of the resulting nickel-based particles doped with 0.01 to 0.5 wt.% of sulfur and is shown in Fig. 4. The physical properties of these particles are shown in Table 2:

15

Table 2: Physical properties of nickel-based particles doped with sulfur

Nickel-based particles doped with sulfur	
BET	7.48 m^2/g
Oxygen content	0.981%
D10	0.125 μm
D50	0.157 μm

Example 3

[105] In this example, the process of Example 2 was repeated with argon carrier gas flow rate of 7.5 L/min and additive gas (oxygen) flow rate of 1.0 L/min and quench gas at 8000 L/min. SEM images are shown in Figs. 5A-5C. The particle size distribution (PSD) of the composition before classification is reproduced in Table 3 whereas the PSD of the composition post-classification to obtain a D50 of 80 nm is reproduced in Table 4:

5

Table 3

D50 (nm)	88
D90 (nm)	195
D99 (nm)	329
BET (m ² /g)	7.77
Particle shape	Spherical
Carbon content (wt.%)	0.019
Oxygen content (wt.%)	1.1

Table 4

Statistics		
Minimum:	15	nm
Maximum:	301	nm
Mean:	88,3	nm
Std Dev.:	43,5	nm
Sum:	157728	nm
Count:	1786	
Under:	0	
Over:	0	
Accepted:	100,0	%
Field Count:	4	
Field Area:	7584892	nm ²
Total Area:	30,339570+06	nm ²
D10:	42	nm
D50:	79	nm
D90:	146	nm
D01	23	nm
D99	227	nm

Example 4

- 10 [106] In this example, the process of Example 2 was repeated with argon carrier gas flow rate of 7.5 L/min and additive gas (oxygen) flow rate of 0.6 L/min and quench gas at 8000 L/min. The particle size distribution (PSD) of the composition before classification is reproduced in Table 5:

15

5

Table 5

D50 (nm)	95
D90 (nm)	169
D99 (nm)	300
BET (m ² /g)	5.71
Particle shape	Spherical
Carbon content (wt.%)	0.050
Oxygen content (wt.%)	0.687

Example 5

[107] In this example, the process of Example 2 was repeated with argon carrier gas flow rate of 5 L/min and additive gas (oxygen) flow rate of 1.0 L/min and quench gas at 1200 L/min.

10 The particle size distribution (PSD) of the composition before classification is reproduced in Table 6:

Table 6

D50 (nm)	72
D90 (nm)	132
D99 (nm)	213
BET (m ² /g)	9.09
Particle shape	Spherical
Carbon content (wt.%)	0.028
Oxygen content (wt.%)	3

Example 6

15 [108] In this example, the process of Example 2 was repeated with argon carrier gas flow rate of 5 L/min and additive gas (oxygen) flow rate of 1.0 L/min and quench gas at 1200 L/min. The particle size distribution (PSD) of the composition before classification is reproduced in Table 6:

20

5

Table 6

D50 (nm)	79
D90 (nm)	146
D99 (nm)	217
BET (m ² /g)	8.87
Particle shape	Spherical
Carbon content (wt.%)	0
Oxygen content (wt.%)	2.6

Example 7

[109] In this example, the process of Example 2 was repeated with argon carrier gas flow rate of 5 L/min and additive gas (oxygen) flow rate of 1.0 L/min and quench gas at 1200 L/min.

10 The particle size distribution (PSD) of the composition before classification is reproduced in Table 7:

Table 7

D50 (nm)	72
D90 (nm)	131
D99 (nm)	201
BET (m ² /g)	10.04
Particle shape	Spherical
Carbon content (wt.%)	0
Oxygen content (wt.%)	3.1

Comparative Example 1

15 [110] In this example, a commercially available product produced by DC-plasma and commercialized as a composition comprising 80 nm nickel-based particles doped with sulfur was analyzed to determine the molecular contents as well as particle size distribution features (FEG SEM, 7 images were analyzed by gridded image analysis, with a total of 2775 particles analyzed). The results are reported in Tables 5-6:

20

5

Table 5

Element	Ni (metal basis)	C	O	S
Method	ICP-MS	LECO	LECO	LECO
Result (wt.%)	99.8	0.15	3.10	0.15

Table 6

Mean (nm)	104
Std Deviation (nm)	50.8
Dmin (nm)	13
D1 (nm)	18
D10 (nm)	43
D50 (nm)	96
D90 (nm)	175
D99 (nm)	242
Dmax (nm)	298
< 20 nm (%)	1.66
> 350 nm (%)	0

Example 8

- 10 [111] In this example, the sintering behavior of nickel-based particles doped with sulfur obtained in Example 3 (sample 2) was compared to the sintering behavior of nickel-based particles without doping agent (samples 1 and 3). The results are produced in Table 7 as well as in Fig. 15.

Table 7

15

Number	Tstart °C	Tend °C	Number of steps	CTE _{100°C} ^{300°C} ppm/K
1	234	621	3	15.5
2	306	994	3...5	
3	153	812	5	13.1

5 [112] These results show that in the composition, the sulfur is effectively incorporated into the nickel-based particles, rather than having a composition with separate sulfur particles and separate nickel particles, since the sintering behavior is changed with the presence of sulfur doping agent.

[113] It should be appreciated that the disclosure is not limited to the particular embodiments
10 described and illustrated herein but includes all modifications and variations falling within the scope of the subject matters as defined in the appended claims.

[114] All references cited in this specification, and their references, are referenced where appropriate for teachings of additional or alternative details, features, and/or technical background.

[115] While the disclosure has been particularly shown and described with reference to
15 particular embodiments, it will be appreciated that variations of the above-disclosed and other features and functions, or alternatives thereof, may be desirably combined into many other different systems or applications. Also, that various presently unforeseen or unanticipated alternatives, modifications, variations or improvements therein may be subsequently made by those skilled in the art which are also intended to be encompassed by the embodiments described
20 herein.

[116] Other examples of implementations will become apparent to the reader in view of the teachings of the present description and as such, will not be further described here.

[117] Note that titles or subtitles may be used throughout the present disclosure for convenience of a reader, but in no way these should limit the scope of the invention. Moreover,
25 certain theories may be proposed and disclosed herein; however, in no way they, whether they are right or wrong, should limit the scope of the invention so long as the invention is practiced according to the present disclosure without regard for any particular theory or scheme of action.

[118] It will be understood by those of skill in the art that throughout the present specification, the term “a” used before a term encompasses embodiments containing one or more
30 to what the term refers. It will also be understood by those of skill in the art that throughout the present specification, the term “comprising”, which is synonymous with “including,”

- 5 “containing,” or “characterized by,” is inclusive or open-ended and does not exclude additional, un-recited elements or method steps.

[119] Unless otherwise defined, all technical and scientific terms used herein have the same meaning as commonly understood by one of ordinary skill in the art to which this invention pertains. In the case of conflict, the present document, including definitions will control.

- 10 [120] As used in the present disclosure, the terms “around”, “about” or “approximately” shall generally mean within the error margin generally accepted in the art. Hence, numerical quantities given herein generally include such error margin such that the terms “around”, “about” or “approximately” can be inferred if not expressly stated.

- 15 [121] Although various embodiments of the disclosure have been described and illustrated, it will be apparent to those skilled in the art in light of the present description that numerous modifications and variations can be made. The scope of the invention is defined more particularly in the appended claims.

CLAIMS:

1. A process for producing doped metallic nanoparticles, the process comprising the steps of:
 - a) preparing metallic microparticles comprising:
 - mixing a liquid doping agent with metal at a temperature sufficient to react the doping agent with the metal and heating to a temperature to melt the metal to obtain a molten metal-doping agent mixture; and
 - obtaining metallic microparticles by atomization of the molten metal-doping agent mixture, wherein the metallic microparticles have the doping agent distributed therein; and
 - b) preparing metallic nanoparticles comprising:
 - evaporating the metallic microparticles to produce a metallic vapor; and
 - cooling the metallic vapor;

wherein cooling of the metallic vapor condensates the metal and the doping agent to produce the doped metallic nanoparticles.

2. The process according to claim 1, wherein the doped metallic nanoparticles are sieved and/or gas-classified to obtain a particle size distribution (PSD) within the range of 20 nm and 300 nm.
3. The process according to claim 1 or 2, wherein the doping agent is uniformly distributed throughout the metallic microparticles.
4. The process according to claim 1 or 2, wherein the doping agent is non-uniformly distributed throughout the metallic microparticles.
5. The process according to any one of claims 1 to 4, wherein the step a) further comprises heating the doping agent to obtain the liquid doping agent.
6. The process according to any one of claims 1 to 5, wherein the atomization is gas atomization.

7. The process according to any one of claims 1 to 6, wherein the metallic microparticles are sieved and/or gas-classified.
8. The process according to any one of claims 1 to 6, wherein the metallic microparticles are gas-classified.
9. The process according to claim 7 or 8, wherein gas-classification is performed with a cyclone.
10. The process according to any one of claims 1 to 9, wherein the evaporating is performed using a plasma torch.
11. The process according to claim 10, wherein the plasma torch is an inductively coupled plasma torch.
12. The process according to claim 10, wherein the plasma torch is a direct current plasma torch.
13. The process according to any one of claims 1 to 12, wherein the metallic nanoparticles have an average size within the range of from about 0.1 nm to about 200 nm.
14. The process according to any one of claims 1 to 12, wherein the metallic nanoparticles have an average size below about 200 nm.
15. The process according to any one of claims 1 to 12, wherein the metallic nanoparticles have an average size below about 120 nm.
16. The process according to any one of claims 1 to 12, wherein the metallic nanoparticles have an average size below about 100 nm.
17. The process according to any one of claims 1 to 12, wherein the metallic nanoparticles have an average size below about 80 nm.

18. The process according to any one of claims 1 to 17, wherein the metallic microparticles have a carbon content of less than about 500 ppm.
19. The process according to any one of claims 1 to 18, wherein the metallic microparticles have a doping agent content of less than about 5000 ppm.
20. The process according to any one of claims 1 to 19, wherein the metallic microparticles have a D50 in the range of between about 1 micron and about 25 microns.
21. The process according to any one of claims 1 to 20, wherein the metallic microparticles have a D90 lower than about 50 μm .
22. The process according to any one of claims 1 to 20, wherein the metallic microparticles have a specific surface area as measured by Brunauer-Emmett-Teller adsorption method (BET) of at least about 0.15 m^2/g .
23. The process according to any one of claims 1 to 22, wherein the metallic microparticles have an oxygen content of less than about 5%.
24. The process according to any one of claims 1 to 23, wherein the metal is selected from silver, copper, lead, palladium, platinum, nickel, gold, cobalt, iron, cadmium, zirconium, molybdenum, rhodium, ruthenium, tantalum, titanium, tungsten, zirconium, niobium, and alloys thereof.
25. The process according to any one of claims 1 to 24, wherein the metal is nickel.
26. The process according to claim 24, wherein the doped metallic nanoparticles are doped nickel nanoparticles.
27. The process according to any one of claims 1 to 26, wherein the doping agent is sulfur.

28. The process according to any one of claims 1 to 26, wherein the doped metallic nanoparticles are sulfur-doped nickel nanoparticles.
29. The process according to any one of claims 1 to 28, wherein the mixing of step a) is performed in a furnace.
30. The process according to any one of claims 1 to 29, wherein the microparticles are fed into a vaporization device for performing the vaporization step.
31. The process according to claim 29, wherein the microparticles are fed into the vaporization device at a feeding rate of 10 to 35 g/minute.
32. The process according to claim 31, wherein the feeding rate does not vary in time by more than 1%.
33. The process according to any one of claims 30 to 32, wherein the microparticles are fed into the vaporization device using a carrier gas.
34. The process according to claim 33, wherein the carrier gas has a flow rate ≤ 10 L/minute.
35. The process according to claim 34, wherein the carrier gas flow rate does not vary in time by more than 1%.
36. The process according to any one of claims 1 to 35, further comprising contacting the vapor with an additive gas, the additive gas causing formation of a layer on the surface of particles.
37. The process according to claim 36, wherein the additive gas includes oxygen and the layer is an oxide layer.
38. The process according to claim 36 or 37, wherein the additive gas has a flow rate in the range of 0.5 to 1.5 L/minute.
39. The process according to claim 38, wherein the additive gas flow rate does not vary in time by more than 1%.

40. The process according to any one of claims 36 to 39, wherein the layer has a thickness of less than 15 nm.
41. The process according to any one of claims 1 to 40, wherein the cooling is performed to reduce temperature of the vapor to below 350 °C.
42. The process according to any one of claims 1 to 41, wherein the cooling is performed with a quench gas.
43. The process according to claim 42, wherein the quench gas has a flow rate in the range of 1000 to 8000 L/minute.
44. The process according to claim 43, wherein the quench gas flow rate does not vary in time by more than 1%.
45. A multilayer ceramic capacitor comprising:
 - a ceramic body including dielectric layers;
 - a plurality of internal electrodes formed in the ceramic body, having dielectric layers interposed therebetween and including the metallic nanoparticles as defined in any one of claims 1 to 44 electrically connected to the internal electrodes.
46. A system for producing doped metallic nanoparticles, comprising:
 - a) a first atomization unit for preparing metallic microparticles comprising:
 - a first unit for mixing a liquid doping agent with metal at a temperature sufficient to react the doping agent with the metal and heating to a temperature to melt the metal to obtain a molten metal-doping agent mixture; and
 - a second unit in fluid communication with the first unit, the second unit being configured for obtaining metallic microparticles by atomization of the molten metal-doping agent mixture, wherein the metallic microparticles have the doping agent distributed therein; and
 - b) a second atomization unit for preparing metallic nanoparticles comprising:

- a first unit for receiving and evaporating the metallic microparticles to produce a metallic vapor; and
- a second unit in fluid communication with the first unit, the second unit being configured for receiving and cooling the metallic vapor;

wherein cooling of the metallic vapor condensates the metal and the doping agent to produce the doped metallic nanoparticles.

47. The system according to claim 46, further comprising a first powder collector configured such that the metallic microparticles are collected from the second unit into the powder collector.
48. The system according to claim 47, wherein the first powder collector includes a sieving and/or a gas-classification device.
49. The system according to claim 48, wherein the gas-classification device includes a cyclone.
50. The system according to any one of claims 47 to 49, further comprising a second powder collector configured such that the doped metallic nanoparticles are collected from the second unit of the second atomization unit into the second powder collector.
51. The system according to claim 50, wherein the second powder collector includes a sieving and/or a gas-classification device.
52. The system according to claim 51, wherein the gas-classification device of the second powder collector includes a cyclone.
53. The system according to any one of claims 46 to 52, wherein the second unit of the first atomization unit includes means for performing gas atomization.
54. The system according to any one of claims 46 to 53, wherein the first unit of the second atomization unit includes a plasma torch.

55. The system according to claim 54, wherein the plasma torch is an inductively coupled plasma torch.
56. The system according to claim 54, wherein the plasma torch is a direct current plasma torch.
57. The system according to any one of claims 46 to 56, being configured for preparing the metallic nanoparticles such as to have an average size within the range of from about 0.1 nm to about 200 nm.
58. The system according to any one of claims 46 to 56, being configured for preparing the metallic nanoparticles such as to have an average size below about 200 nm.
59. The system according to any one of claims 46 to 56, being configured for preparing the metallic nanoparticles such as to have an average size below about 120 nm.
60. The system according to any one of claims 46 to 56, being configured for preparing the metallic nanoparticles such as to have an average size below about 100 nm.
61. The system according to any one of claims 46 to 56, being configured for preparing the metallic nanoparticles such as to have an average size below about 80 nm.
62. The system according to any one of claims 46 to 61, being configured for preparing the metallic microparticles such as to have a carbon content of less than about 500 ppm.
63. The system according to any one of claims 46 to 62, being configured for preparing the metallic microparticles such as to have a doping agent content of less than about 5000 ppm.
64. The system according to any one of claims 46 to 63, being configured for preparing the metallic microparticles such as to have a D50 in the range of between about 1 micron and about 25 microns.

65. The system according to any one of claims 46 to 63, being configured for preparing the metallic microparticles such as to have a D90 lower than about 50 μm .
66. The system according to any one of claims 46 to 63, being configured for preparing the metallic microparticles such as to have a specific surface area as measured by Brunauer-Emmett-Teller adsorption method (BET) of at least about 0.15 m^2/g .
67. The system according to any one of claims 46 to 66, being configured for preparing the metallic microparticles such as to have an oxygen content of less than about 5%.
68. The system according to any one of claims 46 to 67, wherein the metal is selected from silver, copper, lead, palladium, platinum, nickel, gold, cobalt, iron, cadmium, zirconium, molybdenum, rhodium, ruthenium, tantalum, titanium, tungsten, zirconium, niobium, and alloys thereof.
69. The system according to any one of claims 46 to 67, wherein the metal is nickel.
70. The system according to any one of claims 46 to 67, wherein the doped metallic nanoparticles are doped nickel nanoparticles.
71. The system according to any one of claims 46 to 67, wherein the doping agent is sulfur.
72. The system according to any one of claims 46 to 67, wherein the doped metallic nanoparticles are sulfur-doped nickel nanoparticles.
73. The system according to any one of claims 46 to 72, wherein the first unit of the first atomization unit includes a furnace.
74. The system according to any one of claims 46 to 73, being configured for feeding the microparticles into the first unit of the second atomization unit at a feeding rate of 10 to 35 g/minute.

75. The system according to claim 74, being configured for maintaining the feed rate such that the feeding rate does not vary in time by more than 1%.
76. The system according to any one of claims 46 to 75, being configured for feeding the microparticles into the first unit of the second atomization unit using a carrier gas.
77. The system according to claim 76, wherein the carrier gas has a flow rate ≤ 10 L/minute.
78. The system according to claim 77, being configured for maintaining the carrier gas flow rate such that the carrier gas flow rate does not vary in time by more than 1%.
79. The system according to any one of claims 46 to 78, being configured for contacting the metallic vapor with an additive gas, the additive gas causing formation of a layer on the surface of the nanoparticles.
80. The system according to claim 79, wherein the additive gas includes oxygen and the layer is an oxide layer.
81. The system according to claim 79 or 80, being configured for feeding the additive gas at a flow rate in the range of 0.5 to 1.5 L/minute.
82. The system according to claim 81, being configured for maintaining the additive gas flow rate such that the additive gas flow rate does not vary in time by more than 1%.
83. The system according to any one of claims 79 to 82, wherein the layer has a thickness of less than 15 nm.
84. The system according to any one of claims 46 to 83, being configured for performing the cooling so as to reduce temperature of the vapor to below 350 °C.
85. The system according to any one of claims 46 to 84, being configured for performing the cooling with a quench gas.

86. The system according to claim 85, being configured for feeding the quench gas with a flow rate in the range of 1000 to 8000 L/minute.
87. The system according to claim 86, being configured for maintaining the quench gas flow rate such that the quench gas flow rate does not vary in time by more than 1%.

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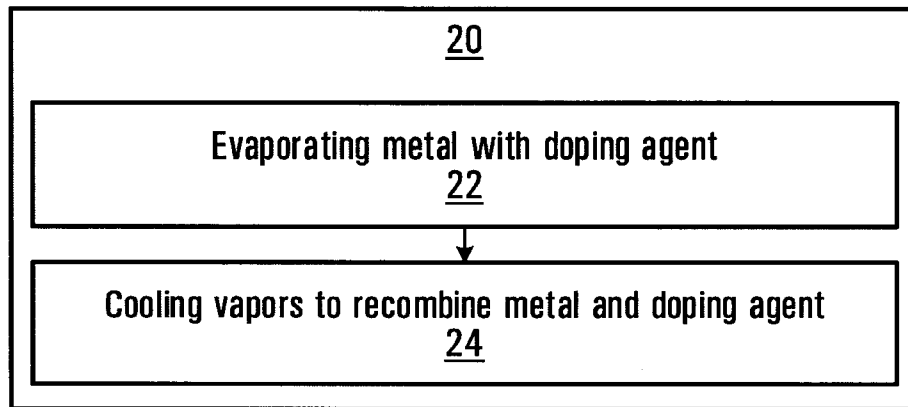


FIG. 1

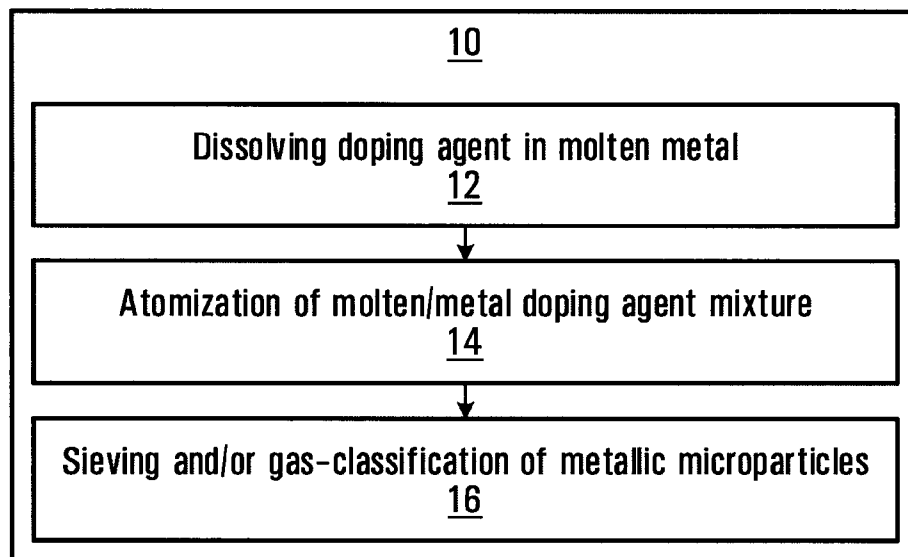


FIG. 2

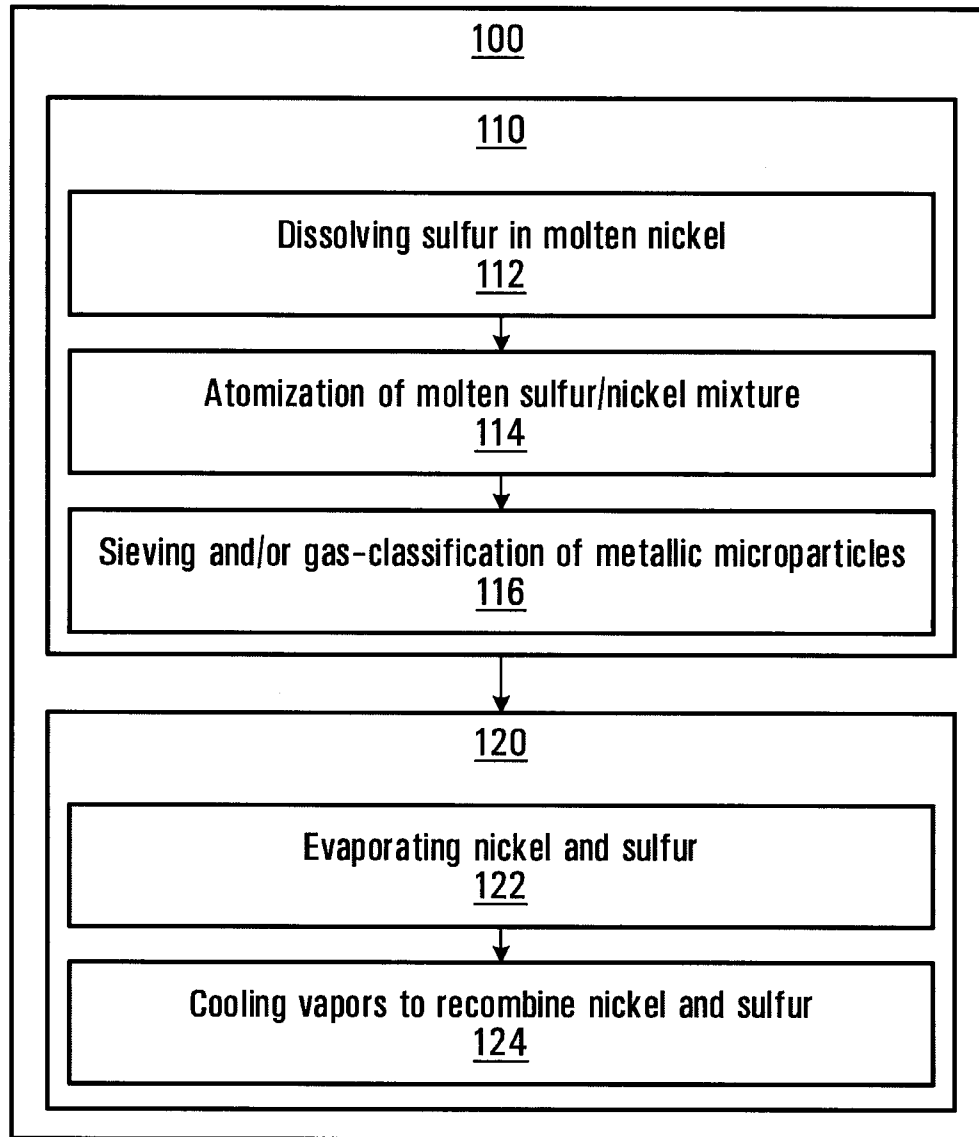


FIG. 3

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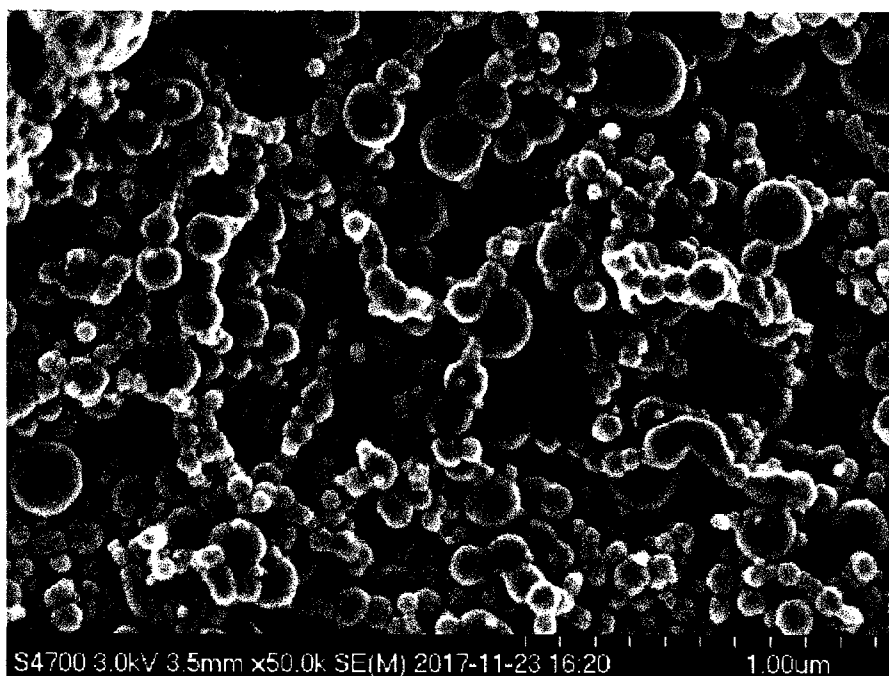


FIG. 4

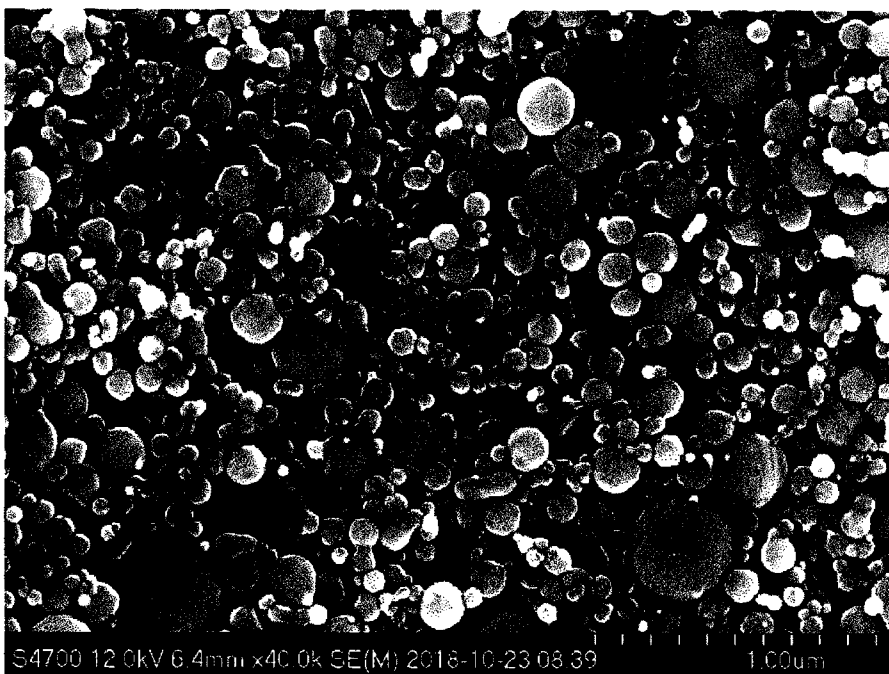


FIG. 5A

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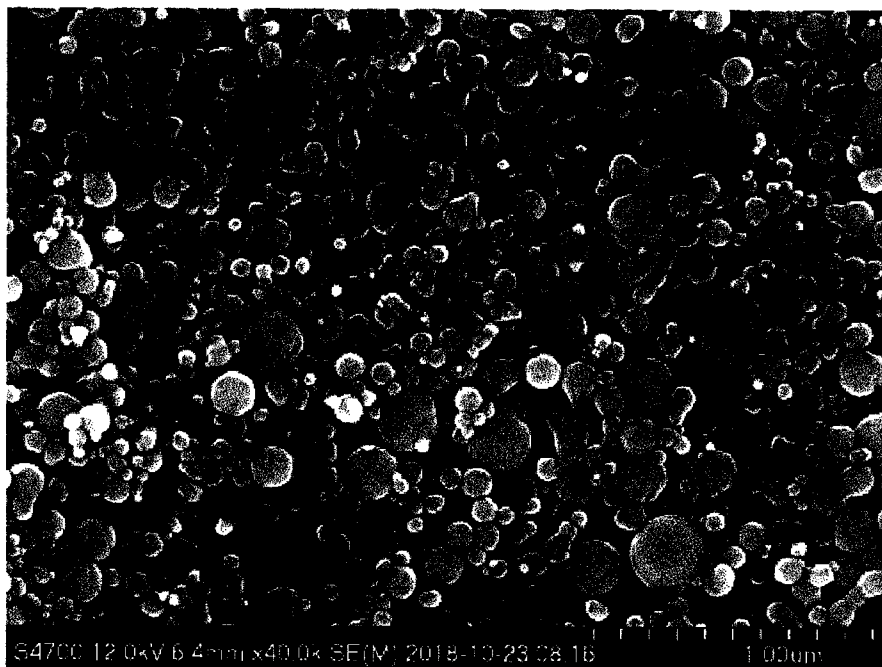


FIG. 5B

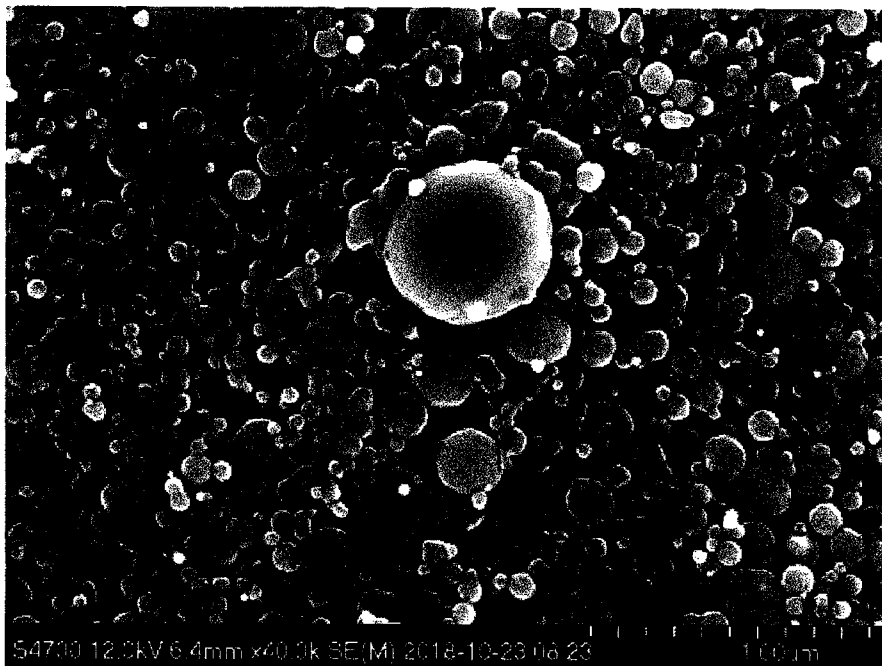


FIG. 5C

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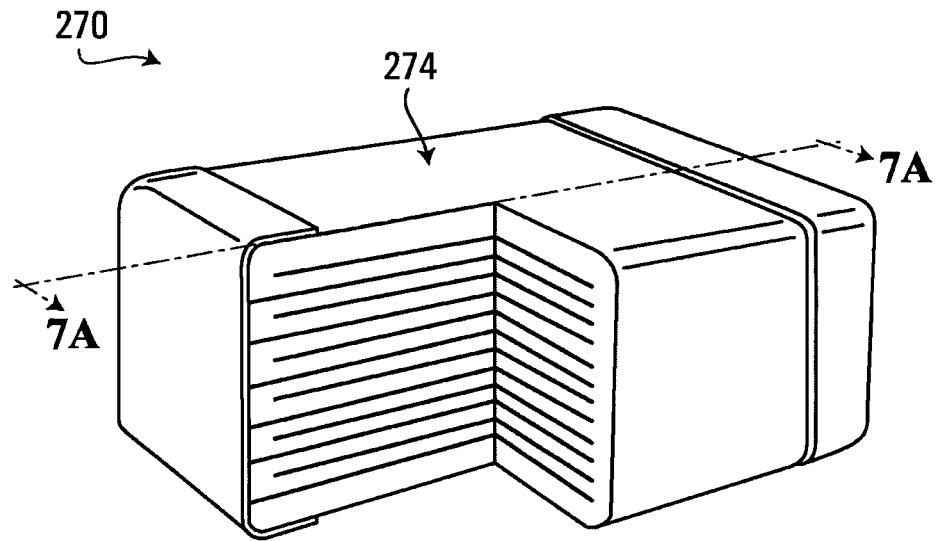


FIG. 6

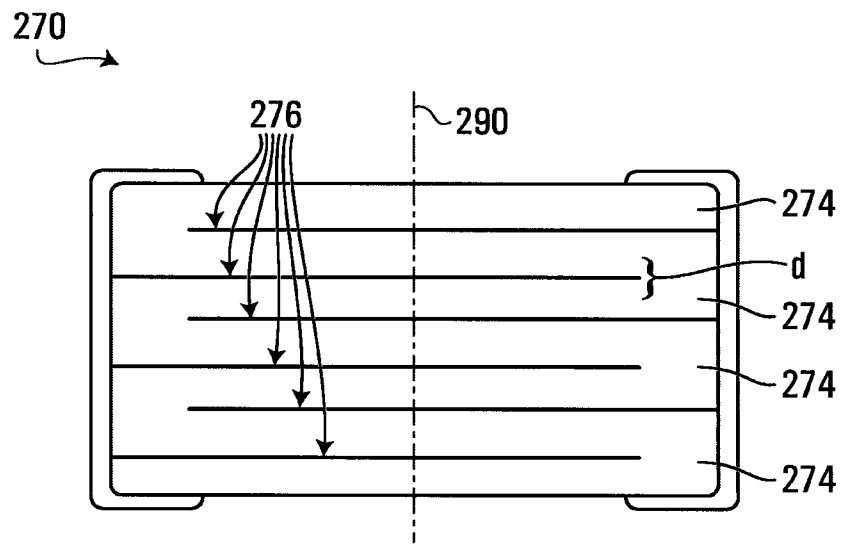


FIG. 7

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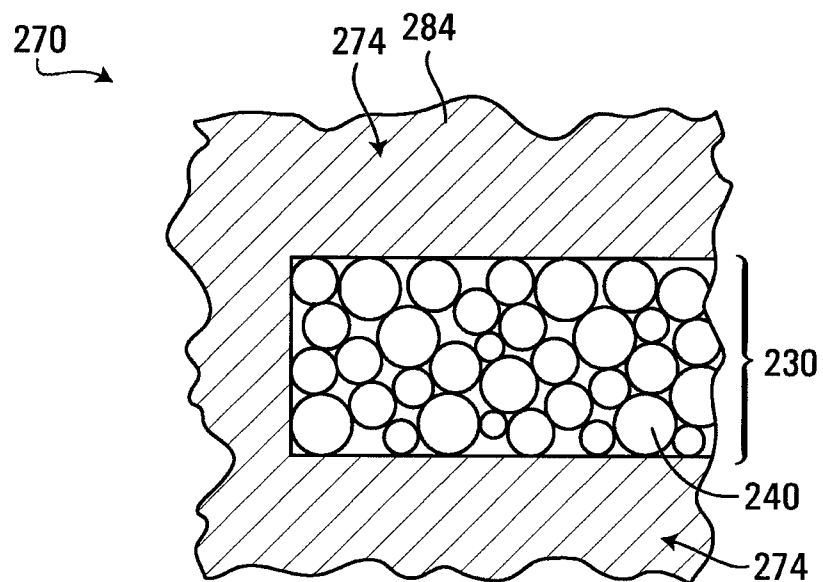


FIG. 8

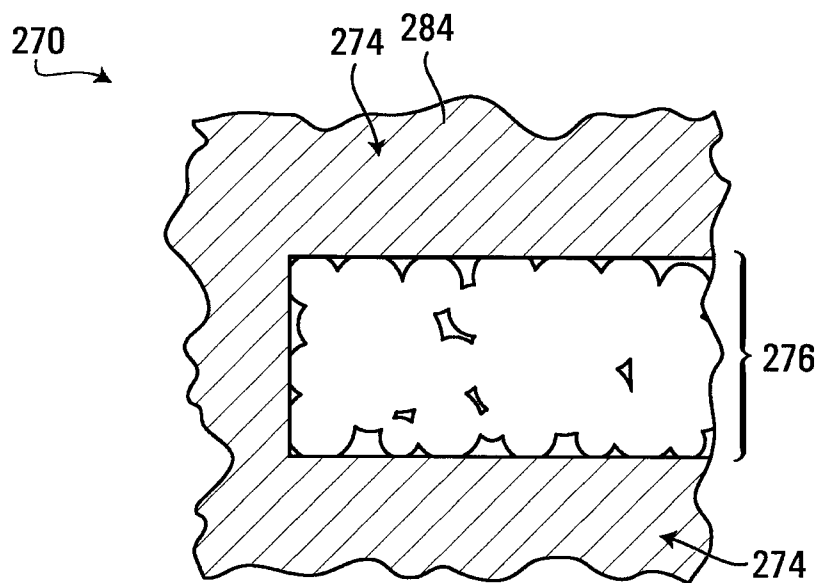


FIG. 9A

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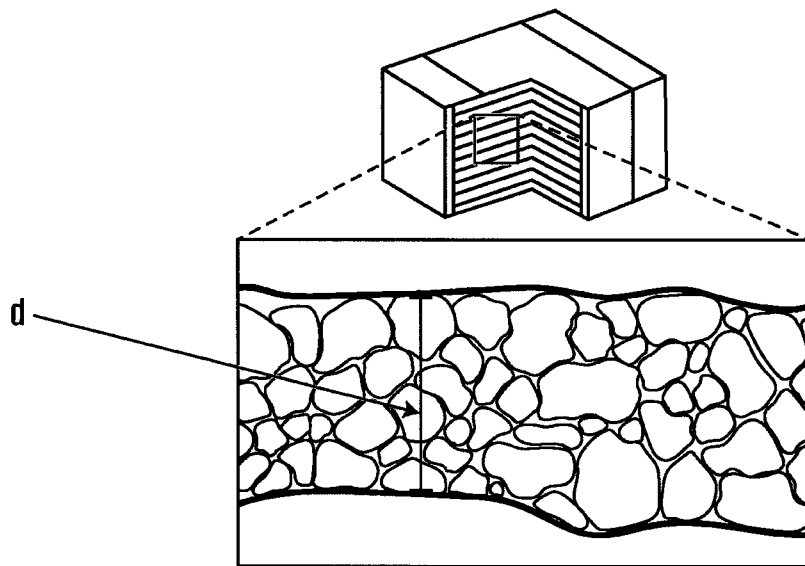


FIG. 9B

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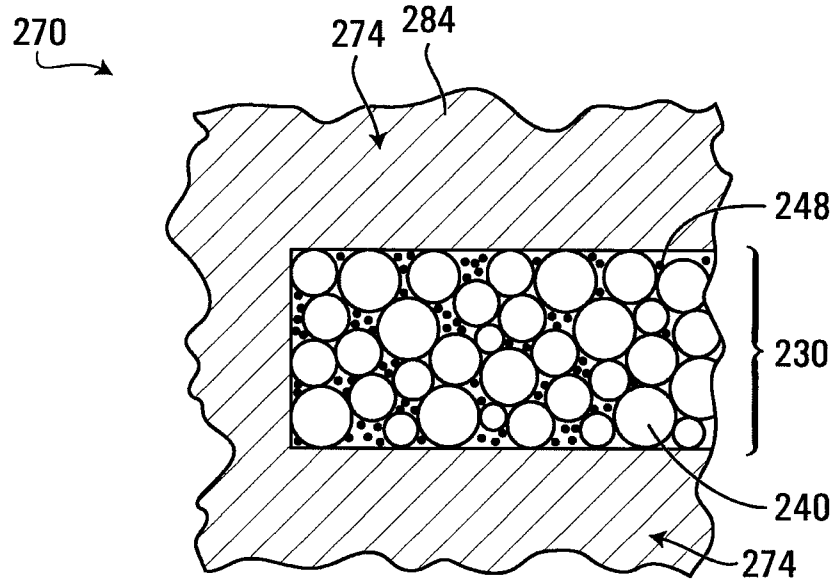


FIG. 10

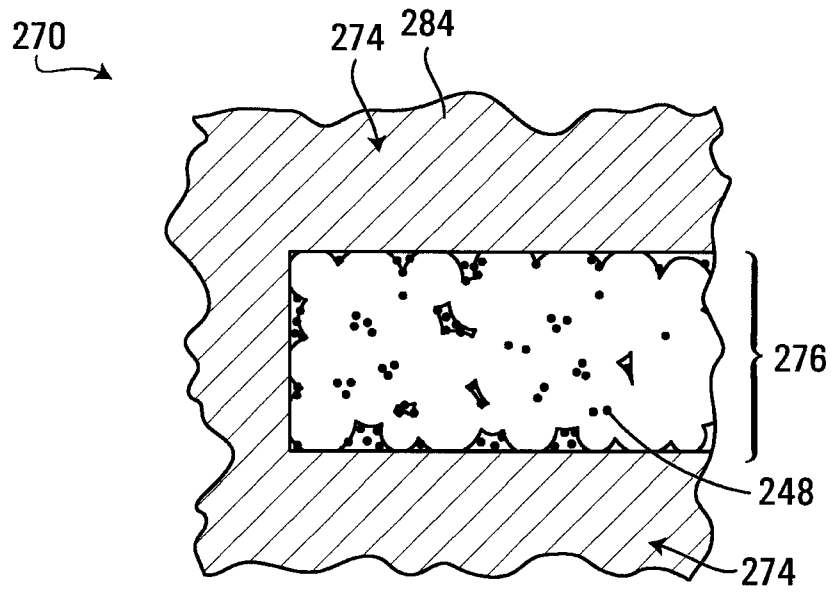


FIG. 11

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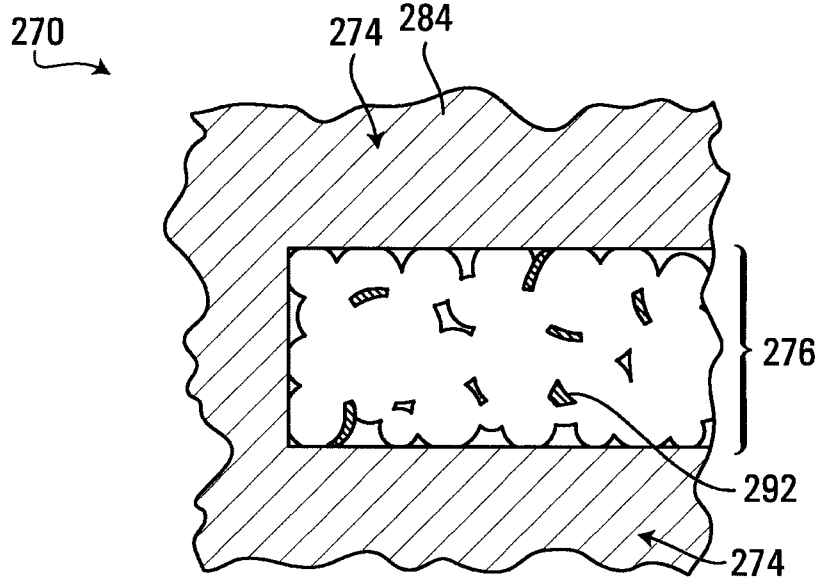


FIG. 12

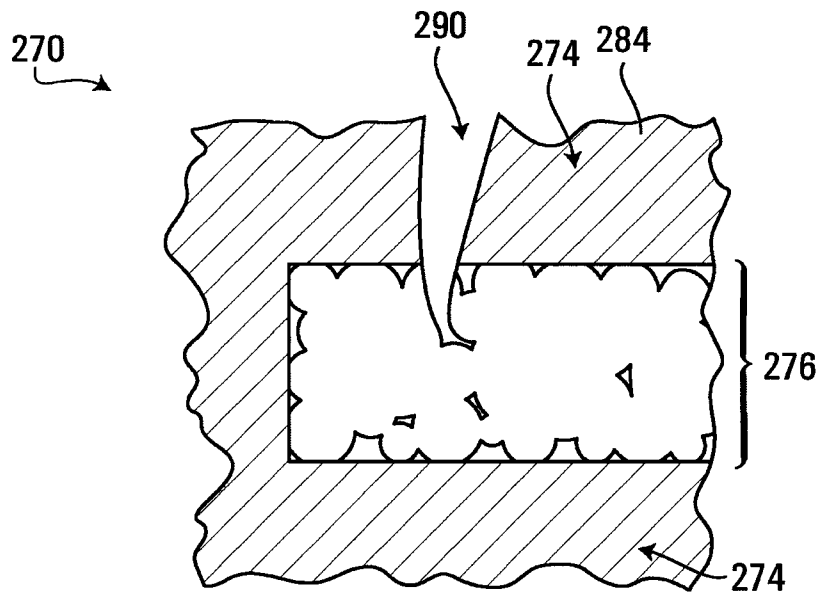


FIG. 13A

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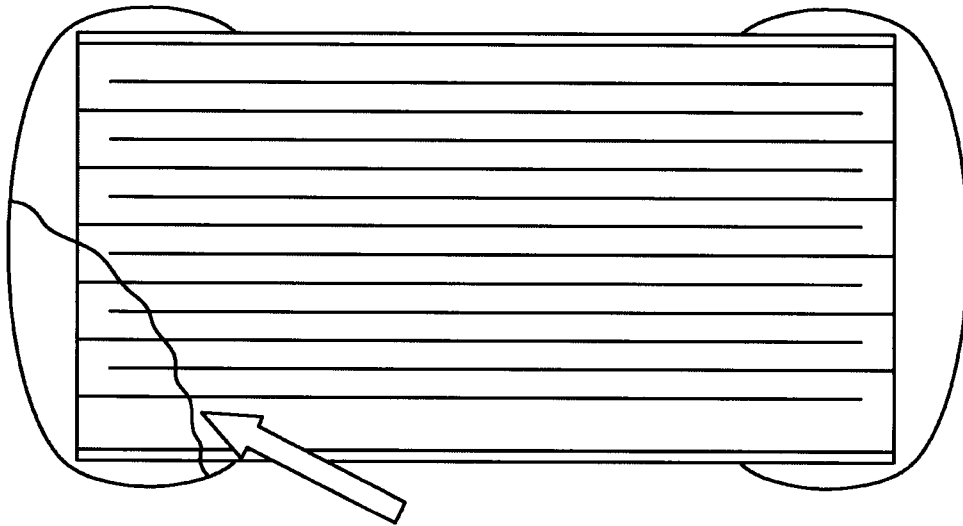


FIG. 13B

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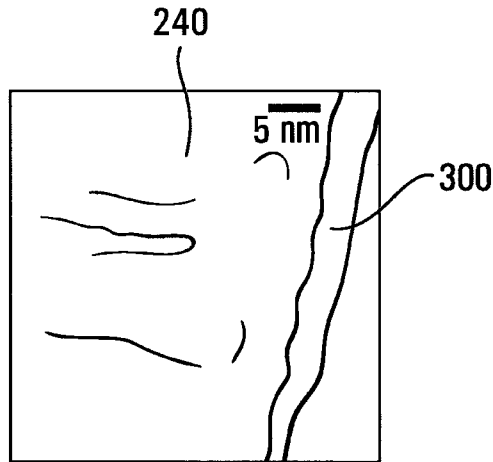


FIG. 14

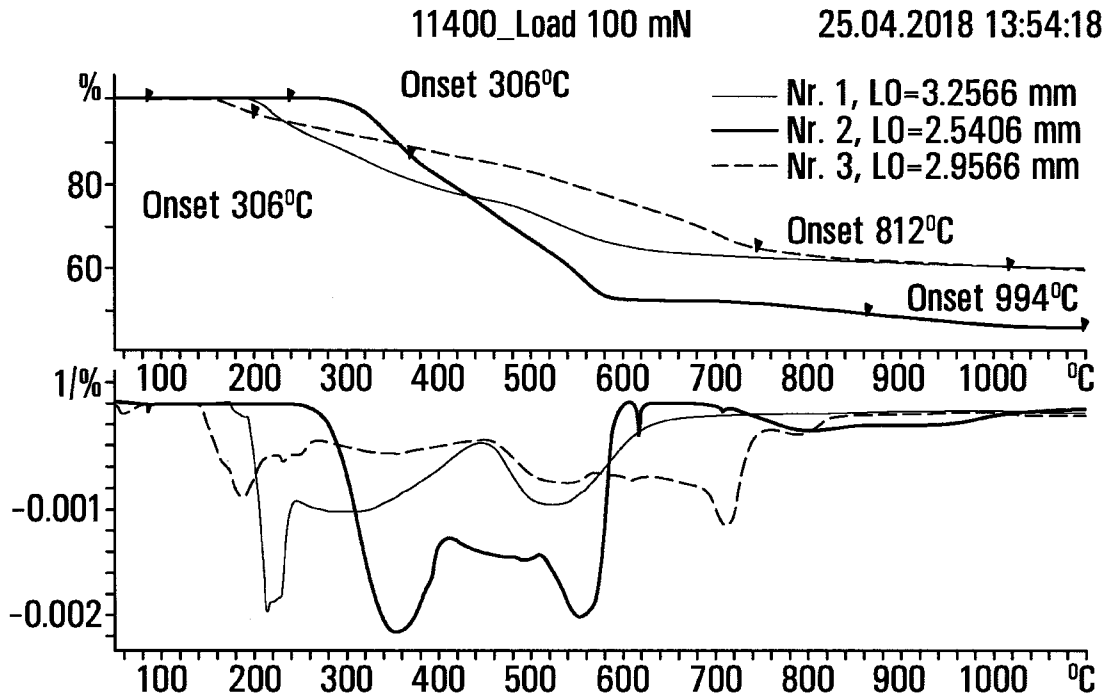


FIG. 15

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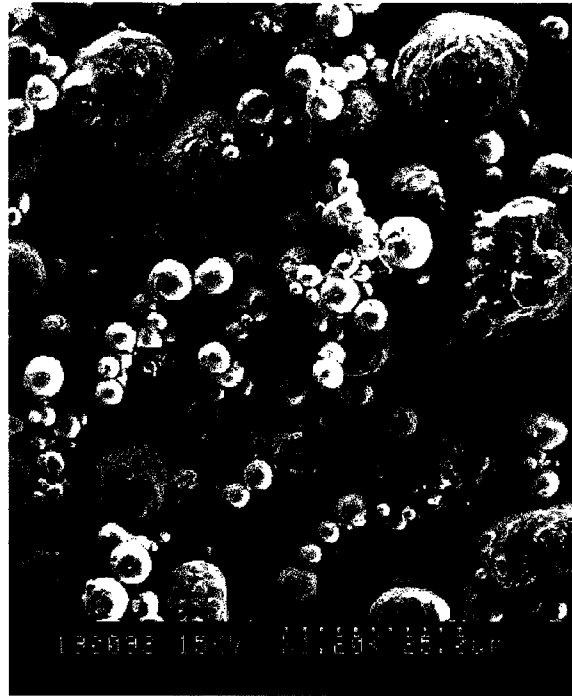


FIG. 16A

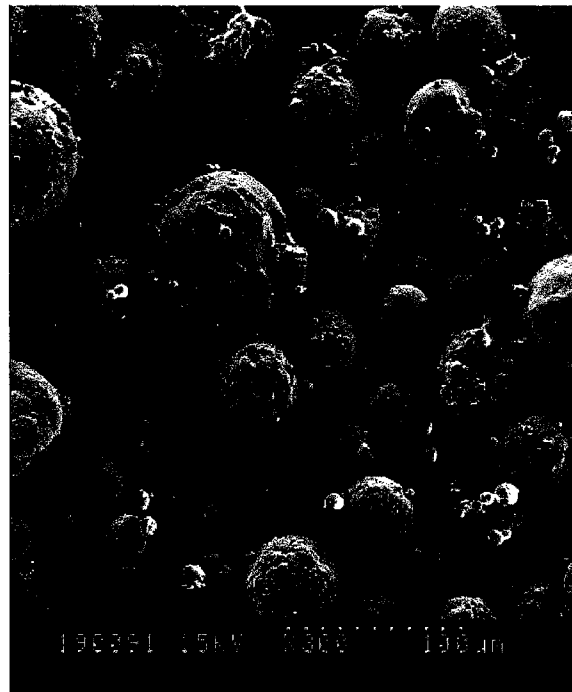


FIG. 16B

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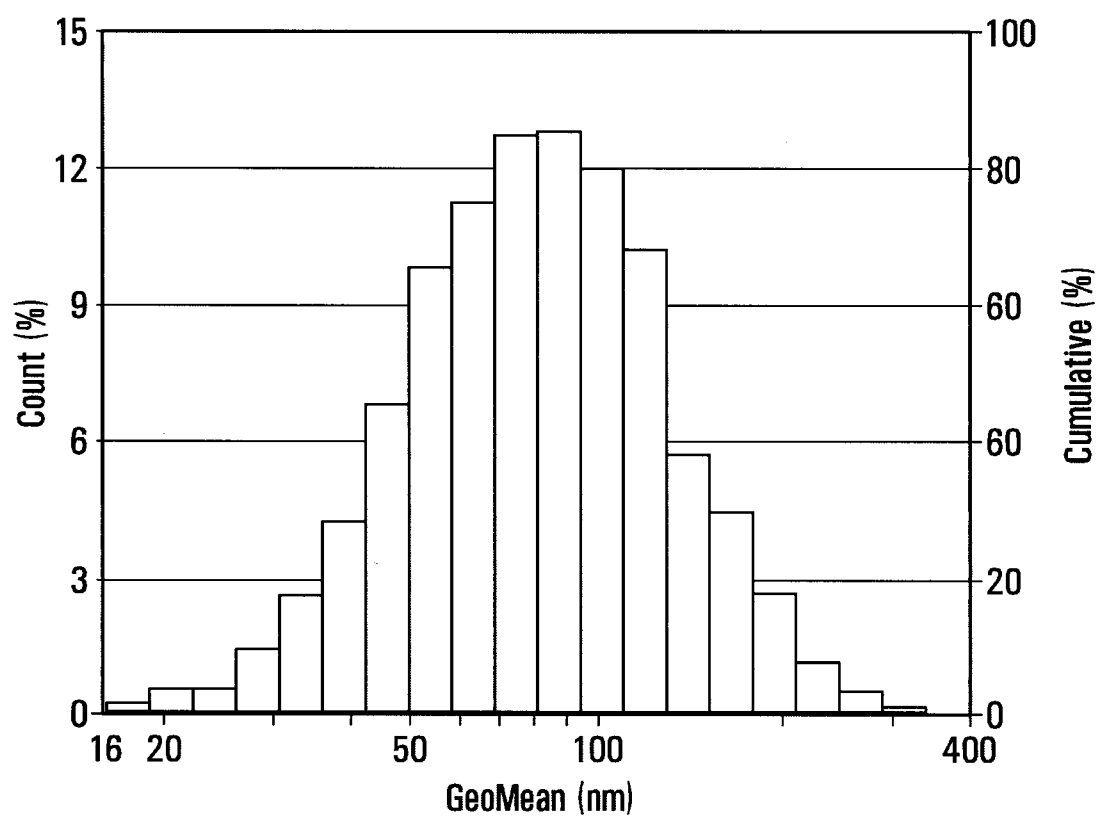


FIG. 17

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Evaporating metal with doping agent

22



Cooling vapors to recombine metal and doping agent

24